

Tunability of the Photoluminescence and Coupled Charge Transfer Dynamics in Monolayer MoS₂ Decorated with WS₂ Quantum Dots

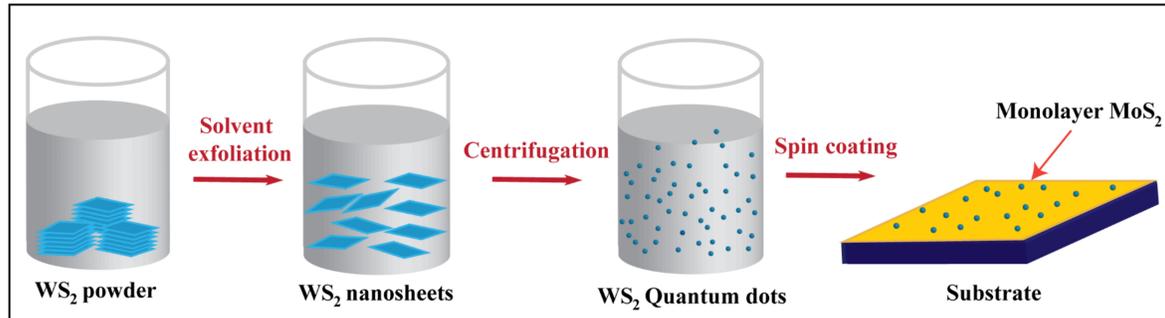
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INTRODUCTION

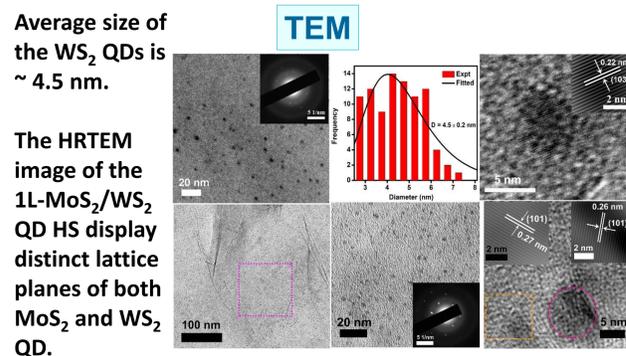
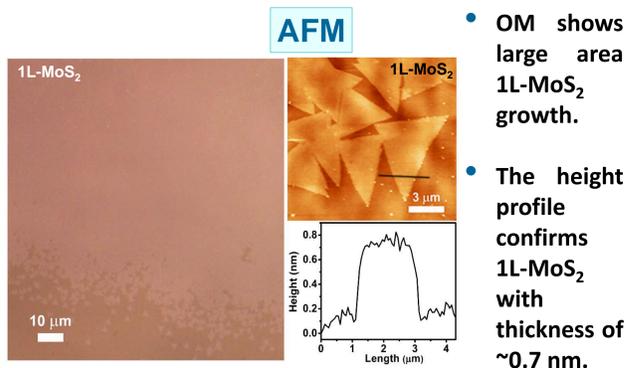
- 0D-2D Heterostructure.
- Tunability of the photoluminescence (PL) of the monolayer MoS₂ (1L-MoS₂).
- Using the four-energy level model, a detailed quantitative analysis involving coupled charge transfer was employed to explain the redshift and the systematic decrease in the intensity of the PL peak in 1L-MoS₂/WS₂ QD heterostructure.

Schematic illustration of the synthesis of WS₂ QDs and their decoration onto 1L-MoS₂

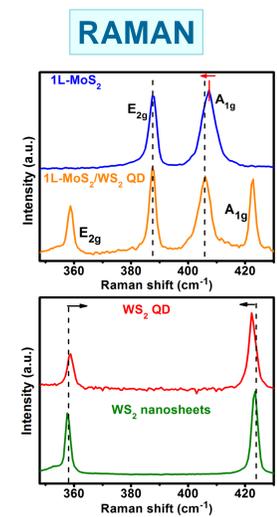
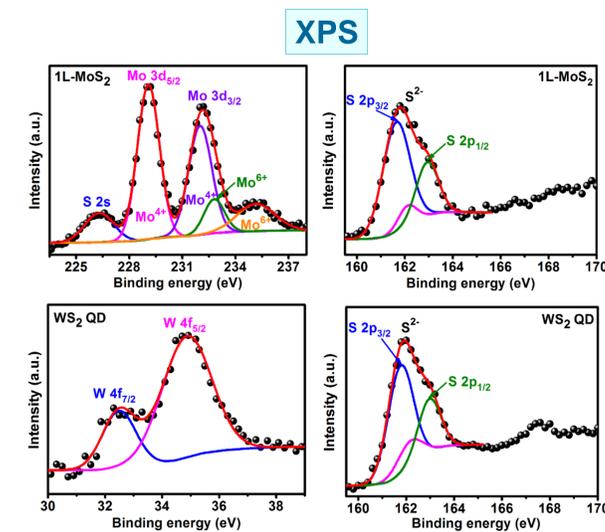


- 1L-MoS₂ were grown by CVD process.
- The WS₂ QDs were spin coated onto 1L-MoS₂ resulting in the formation of HS

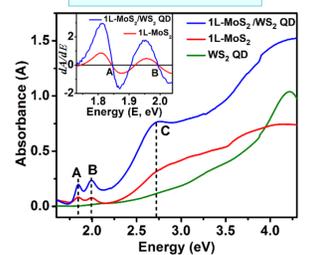
Morphology Characteristics



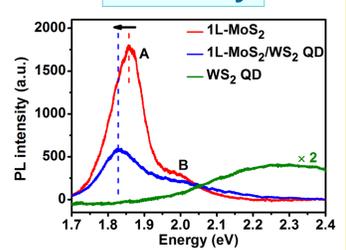
Structural Characteristics



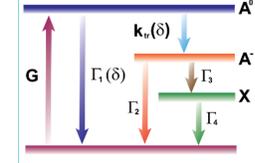
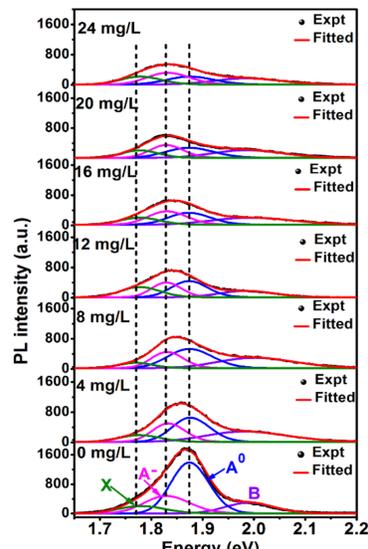
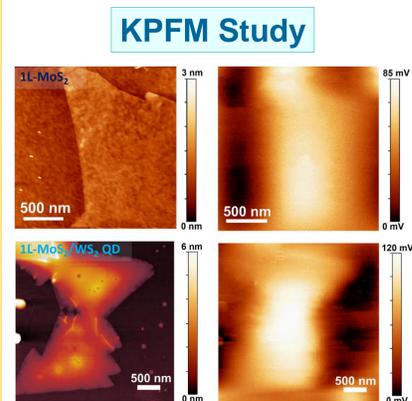
UV-vis Abs



PL Study



Optical Characteristics



The rate equations for the population of neutral excitons N_{A^0} , trions N_{A^-} and the defect bound excitons N_X

$$\frac{dN_{A^0}}{dt} = G - [\Gamma_1 + k_{tr}(\delta)]N_{A^0} \quad (1)$$

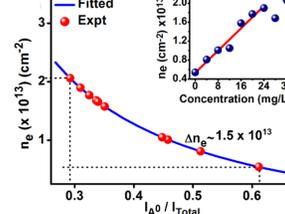
$$\frac{dN_{A^-}}{dt} = k_{tr}(\delta)N_{A^0} - (\Gamma_2 + \Gamma_3)N_{A^-} \quad (2)$$

$$\frac{dN_X}{dt} = \Gamma_3 N_{A^-} - \Gamma_4 N_X \quad (3)$$

$$k_{tr}(\delta) = k_{tr}(0) \left(1 - s \frac{1}{\delta + 1}\right) \quad (4)$$

$$\Gamma_1(\delta) = \Gamma_1(0) (1 + \beta \delta) \quad (5)$$

The steady-state PL intensities of neutral exciton (I_{A^0}), trion (I_{A^-}) and defect bound exciton (I_X)



$$I_{A^0}(n) = \frac{AG\gamma_{ex}}{\Gamma_1(\delta) + k_{tr}(\delta)} \quad (6)$$

$$I_{A^-}(n) = \frac{k_{tr}(\delta)}{(\Gamma_2 + \Gamma_3)} \frac{AG\gamma_{tr}}{(\Gamma_1(\delta) + k_{tr}(\delta))} \quad (7)$$

$$I_X(n) = \frac{\Gamma_3}{\Gamma_4} \frac{k_{tr}(\delta)}{(\Gamma_2 + \Gamma_3)} \frac{AG\gamma_X}{(\Gamma_1(\delta) + k_{tr}(\delta))} \quad (8)$$

Assuming the validity of the law of mass action

$$\frac{N_{A^0} n_e}{N_{A^-}} = \left(\frac{16\pi m_{A^0} m_e}{h^2 m_{A^-}}\right) k_B T \exp\left(-\frac{E_b}{k_B T}\right) \quad (9)$$

$$\frac{I_{A^0}}{I_{total}} = \frac{1}{1 + \frac{\gamma_{tr} N_{A^-}}{\gamma_{ex} N_{A^0}} + \frac{\gamma_X N_X}{\gamma_{ex} N_{A^0}}} \approx \frac{1}{1 + 11.8 \times 10^{-14} n_e} \quad (10)$$

Conclusions

- For pristine 1L-MoS₂, the charge density is $\sim 5.6 \times 10^{12} \text{ cm}^{-2}$
- After WS₂ QD doping, the electron density of the 1L-MoS₂/WS₂ QD HS increases to $21.6 \times 10^{12} \text{ cm}^{-2}$.
- The difference in the electron density before and after the formation of the HS, $\Delta n_e \sim 1.5 \times 10^{13} \text{ cm}^{-2}$.
- Tunability of PL of 1L-MoS₂ with the decoration of WS₂ QDs

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REFERENCES

Larionette P. L. Mawlong, et al., *Sci. Rep.*, 9, 19414 (2019).